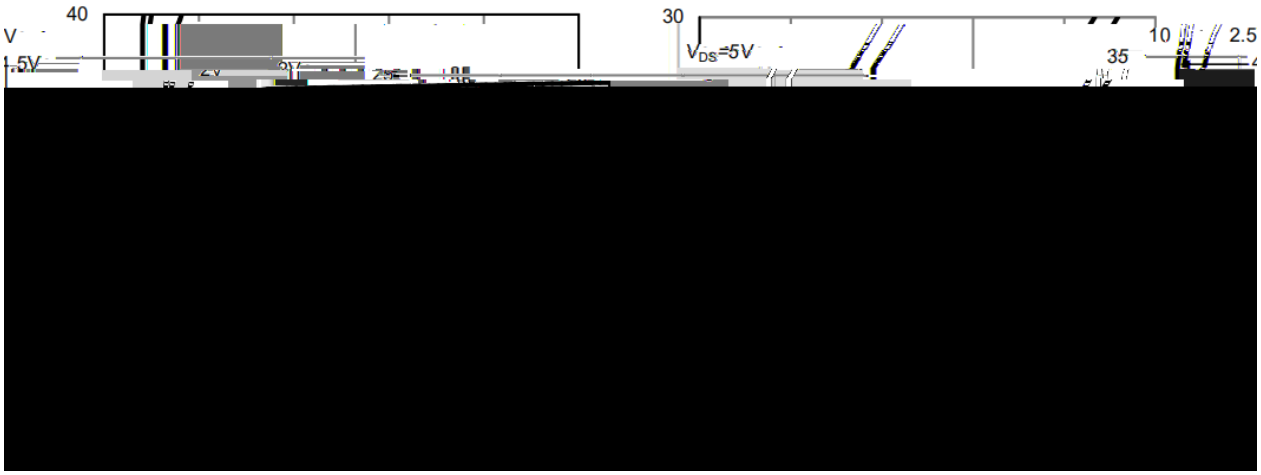
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	20	V
Drain Current		I_D(Tc=25)	8	A
		V_{GS}	±12	V
		I_{AS}	12.5	A
y		E_{AS}	111	mJ
		P_D(Tc=25)	2.8	W
		T_j	150	
		T_{stg}	-55 150	
	t ≤ 10s	R θ JA	45	/W
	Steady-State	R θ JA	80	

	Symbol	Test Conditions		Min	Typ	Max	Unit
	BV_{DSS}	V_{GS}=0V	I_D=250 A	20	25		V
	I_{DSS}	V_{DS}=20V	V_{GS}=0V			1.0	A
		V_{DS}=16V	T_J=150			50	
	I_{GSS}	V_{GS}=±12V	V_{DS}=0V			±0.1	A
	$R_{DS(on)}$	V_{GS}=10V	I_D=8.0A		8	10	m
		V_{GS}=4.5V	I_D=8.0A		9.5	11	m
		V_{GS}=2.5V	I_D=8.0A		14	16	m

17.04 rebg71

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(4.5V)}$	V_{DS}=10V V_{GS}=4.5V I_D=12.0A		17.9		nC
Gate-Source Charge	Q_{gs}			1.5		

/ Electrical Characteristic Curve



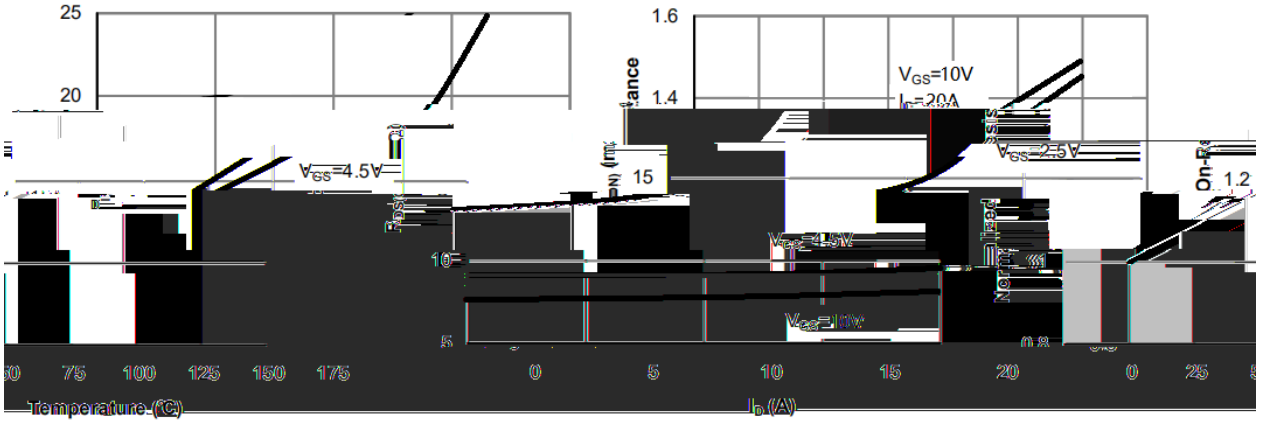


Figure 4: On-Resistance vs. Junction Temperature

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

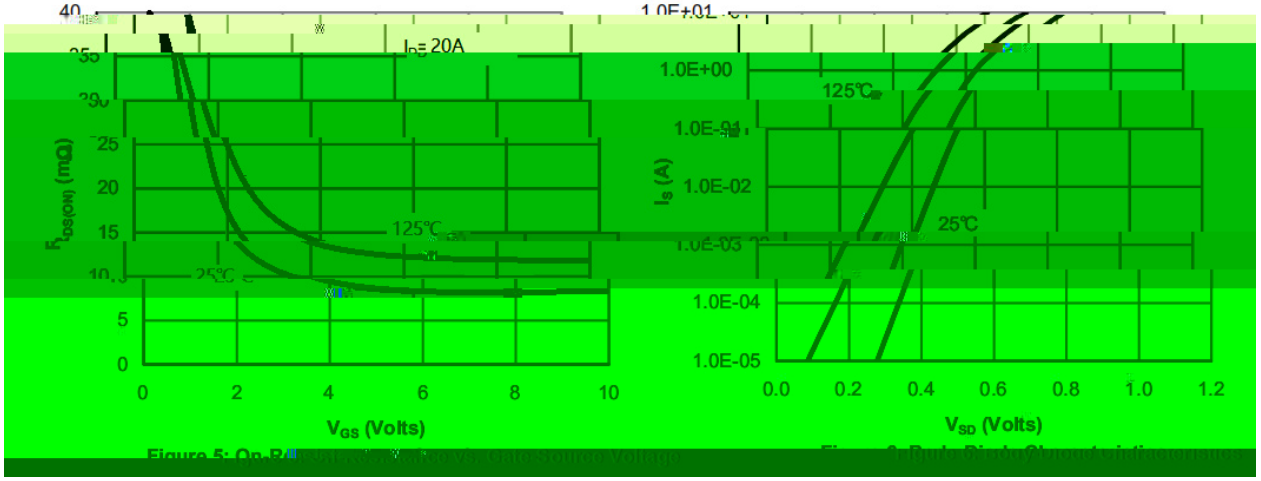


Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

/ Electrical Characteristic Curve

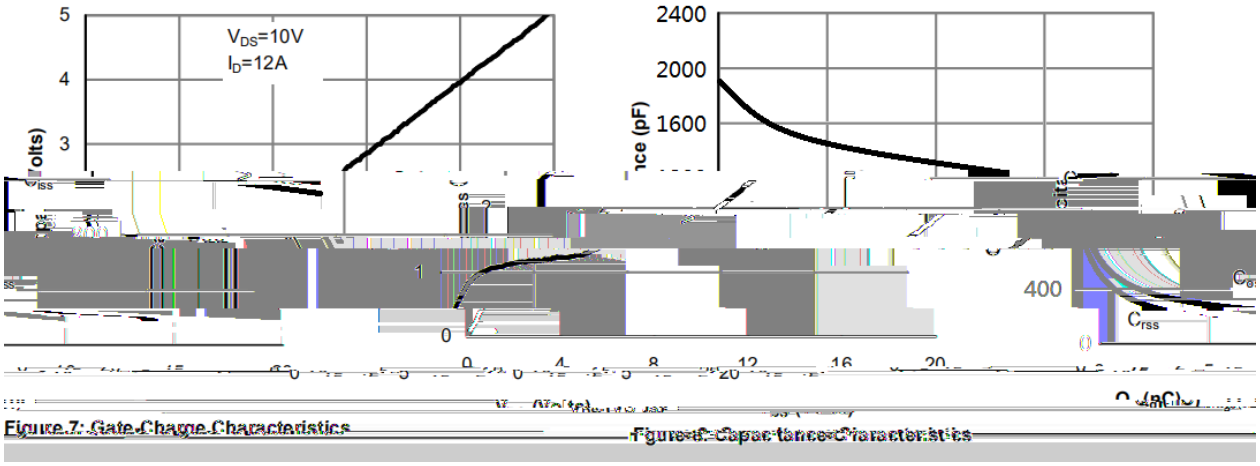
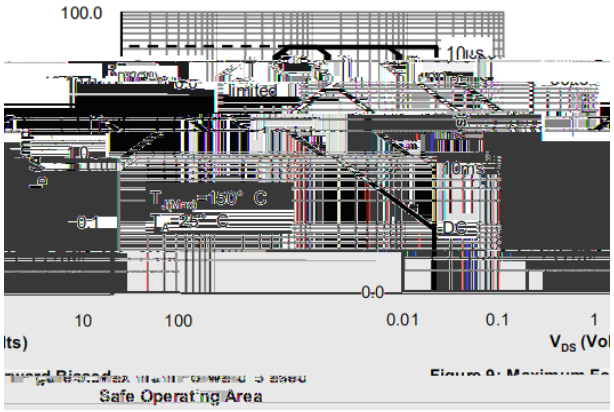
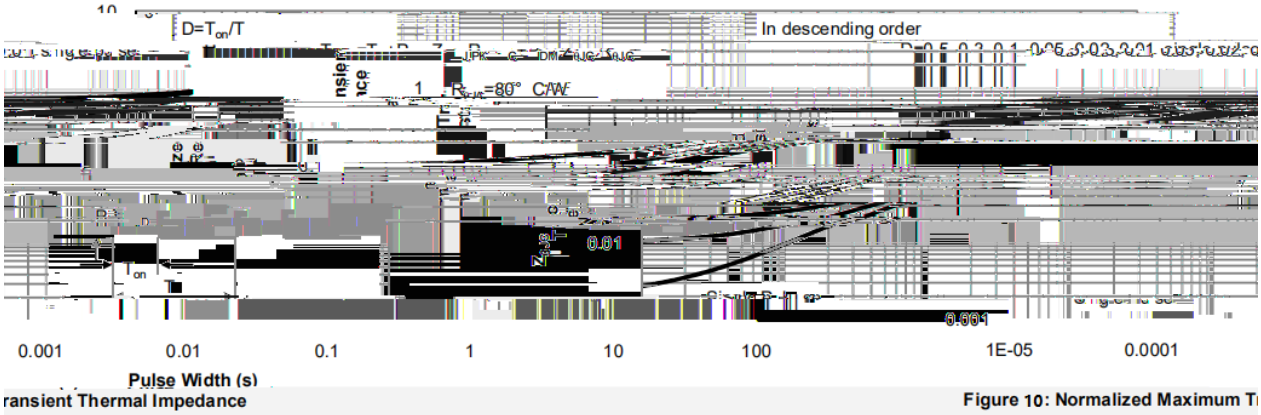


Figure 7: Gate Charge Characteristics

Figure 8: Capacitance Characteristics



Safe Operating Area

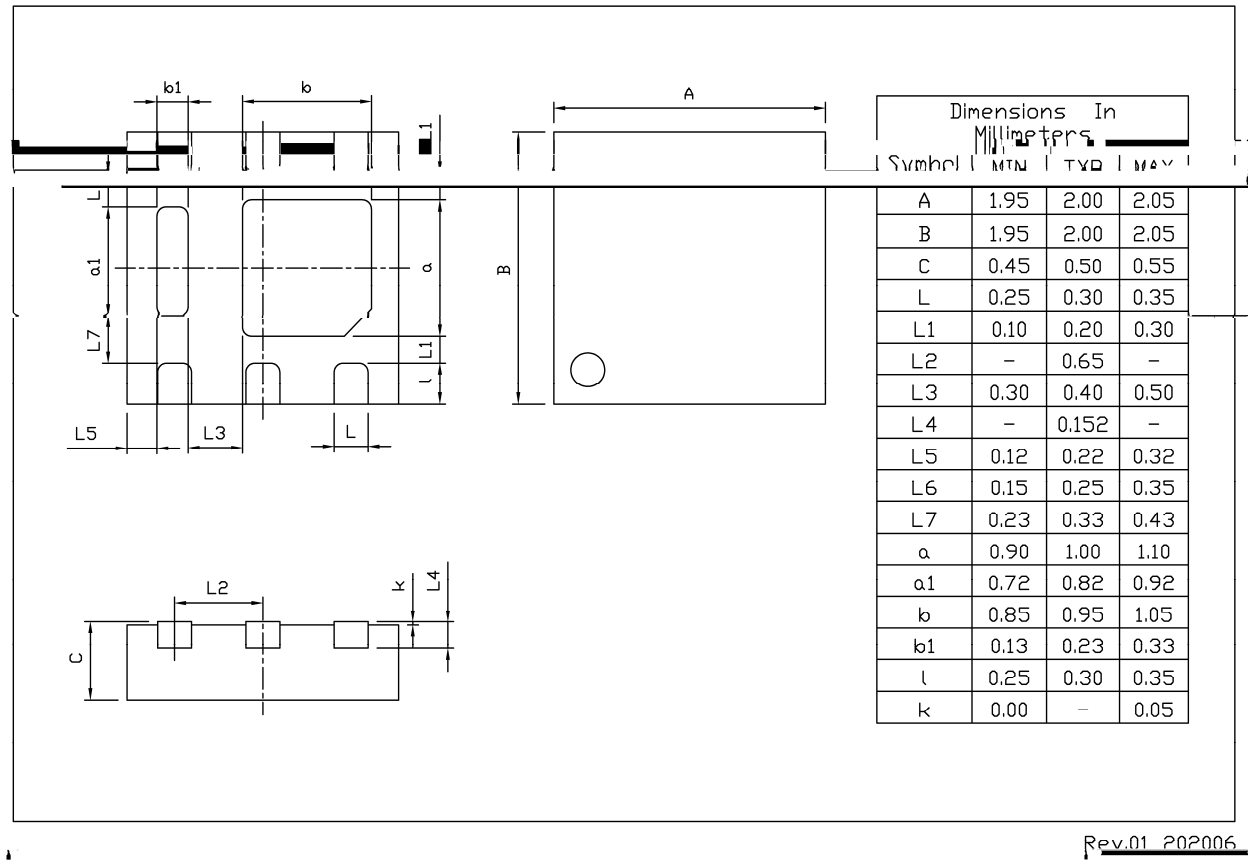


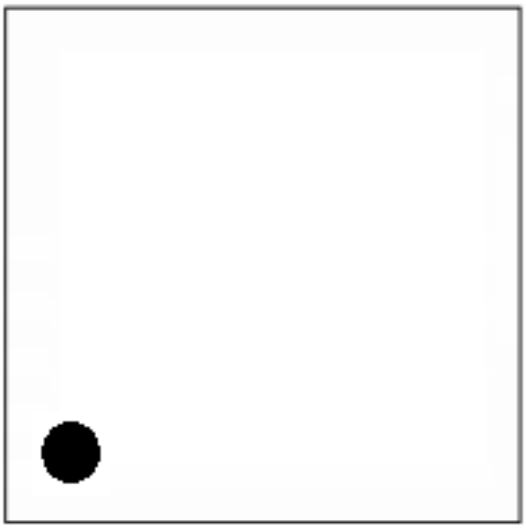
Transient Thermal Impedance

Figure 10: Normalized Maximum T

/ Package Dimensions

DFN2×2B-6L-0.5 Unit:mm



Dimensions In Millimeters			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	–	0.65	–
L3	0.30	0.40	0.50
L4	–	0.152	–
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	–	0.05

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